

REMARKS

Applicants respectfully request favorable reconsideration of this application, as amended.

The specification and the title of the invention have been amended in compliance with the Examiner's requirements. A typographical error on page 29 has also been corrected.

The objection to the Abstract is evidently mistaken, as the indicated informalities are not present in the Abstract.

Without acceding to the rejection under 35 U.S.C. § 112, first paragraph, the claims have been amended for better conformity with the disclosure (which did not specifically call out first to eighth transistors as such). The memory cell transistor structure is shown in Figs. 7 and 19, and is described in the paragraph bridging pages 10 and 11 of the specification. See especially, page 11, lines 10-20. Regarding the use of different gate oxide thicknesses, see, for example, the description of Fig. 22 beginning at page 30, line 6.

As will be appreciated from the foregoing discussion, the objection to the drawings is moot in view of the present amendments.


With all outstanding issues having been fully overcome, Applicants respectfully solicit a Notice of Allowance.

The Commissioner is hereby authorized to charge to Deposit Account No. 50-1165 any fees under 37 C.F.R. §§ 1.16 and 1.17 that may be required by this paper and to credit

any overpayment to that Account. If any extension of time is required in connection with the filing of this paper and has not been requested separately, such extension is hereby requested.

Respectfully submitted,

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CERTIFICATE OF FACSIMILE TRANSMISSION

I hereby certify that this correspondence is being facsimile transmitted to the United States Patent and Trademark Office on the date shown below.

January 12, 2005
Date


Mitchell W. Shapiro